



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Toshiya UEMURA, et al.

Serial No.: 09/559,273

Group Art Unit: 2815

Filed: April 27, 2000

Examiner: Joseph H. Nguyen

For: LIGHT-EMITTING SEMICONDUCTOR DEVICE USING GROUP III
NITRIDE COMPOUND

Honorable Commissioner of Patents
Washington, D.C. 20231
BOX AF

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AMENDMENT UNDER 37 C.F.R. § 1.116

Sir:

In response to the Final Office Action dated September 30, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend the claims to read as follows:

1. (Amended) A flip chip type of light-emitting semiconductor device comprising:
- a substrate;
- group III nitride compound semiconductor layers formed on said substrate, said layers comprising a p-type semiconductor layer; and
- a positive electrode including at least one layer of a first positive electrode layer which is formed on or above said p-type semiconductor layer and reflects light toward said substrate, said first positive electrode layer being made of at least one of silver (Ag), rhodium (Rh), ruthenium (Ru), platinum (Pt), palladium (Pd), and an alloy including at least one of these metals,
- wherein said substrate transmits said light reflected from said positive electrode, and light is emitted from a substrate side of said light-emitting device.

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